

## **Data Sheet**

#### iMOTION™ Motion Controller Module for PM AC Fan

#### **Quality Requirement Category: Industry**

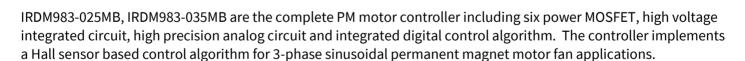
#### **Features**

- Complete 250V 500V 3-phase inverter system in one chip
- Permanent Magnet Sinusoidal Motors Control by Hall sensors
   Only two low cost Hall elements required
- High efficiency control by quadratic phase advance curve
- Internal clock based on external RC
- 15V single power supply3.3V Integrated Voltage Regulator
- Integrated protection features:
   Dynamic overcurrent, Overtemperature,
   Overspeed, Rotor lock, Undervoltage lockout
- Full Three Phase Gate Driver
- Integrated Bootstrap Diodes
- No heatsink required
- 12x12 mm<sup>2</sup> PQFN package

#### **Applications**

• PM fan motor control

# Description



Other than the IRDM982 the IRDM983 only requires two hall sensors.

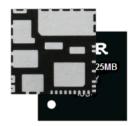
The integrated digital controller does not require any programming.

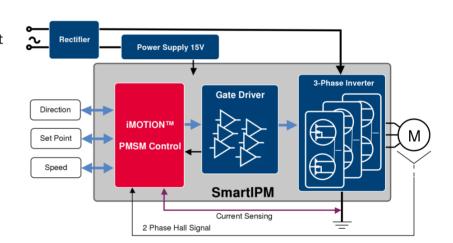
Instead there are 16 load curves stored in the internal ROM that can be selected via two resistor pairs.

The IRDM983 is packaged in the 12 x 12 PQFN package and designed to dissipate the power loss through a PCB without the use of an external heatsink.

There are two products available depending on the power rating of the internal high voltage MOSFETs:

- 1) IRDM983-025MB employs six MOSFETs 500V 2A and 600V high voltage IC
- 2) IRDM983-035MB employs six MOSFETs 500V 3A and 600V high voltage IC





#### PD19082016

## IRDM983-025MB, IRDM983-035MB Complete Motion Controller Module for PM AC fan

#### **Features**

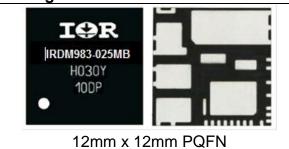
- Complete 500V 3-phase inverter system in one chip
- No heat-sink required
- Permanent Magnet Sinusoidal Motors Control by two Hall sensors
- Selectable 4 or 12 pulse output per revolution<sup>1)</sup>
- High efficiency control by quadratic phase advance curve
- Internal clock based on external RC
- 15V single power supply
- 3.3V Integrated Voltage Regulator
- Dynamic overcurrent limit per temperature
- Over-temperature control
- Over-speed protection
- Rotor lock detection/protection
- Full Three Phase Gate Driver
- Integrated Bootstrap Diodes
- Under-voltage lockout

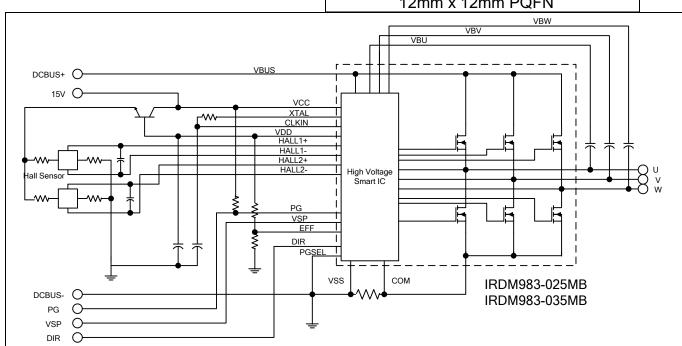
Typical ApplicationsFan motor control

#### **Product Summary**

Topology	3 Phase AC
V <sub>OFFSET</sub>	≤ 500 V for IRDM983- 025MB, IRDM983-035MB
Control	Phase Advancement control
Feedback	DC Bus shunt, 2 Hall sensor
Temperature sensor	Integrated

#### **Package**





1) When used with 8 poles motor. In general it is 1 pulse / 3 pulses per electrical revolution.

## **Revision History**

- Created new DS (April, 2015)
   Fixed part numbers typo (5 May 2015)
  - Updated ESD level (19 August 2016)

# International IRI TOR Rectifier

## IRDM983-025MB, IRDM983-035MB

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#### Introduction

IRDM983-025MB, IRDM983-035MB are the complete PM motor controller including six power MOSFET, high voltage integrated circuit, high precision analog circuit and digital control algorithm. There are two products depending on power rating of internal high voltage MOSFET listed below:

- 1) IRDM983-025MB employs six MOSFET 500V 2A and 600V high voltage IC
- 2) IRDM983-035MB employs six MOSFET 500V 3A and 600V high voltage IC

All two products are packaged in the 12 x 12 PQFN package and designed to dissipate the power loss through a mating PCB without an external heatsink. All two products contain exactly same control algorithm and analog functions. The controller implements a two Hall sensors based control algorithm for 3-phase sinusoidal permanent magnet motor fan applications. The control also employs high efficiency PM motor control algorithm based on a quadratic load curve stored in internal ROM. 16 possible curves are selectable.

All devices have an on-chip voltage regulator to derive the 3.3V, required by the digital logic, from the 15V (VCC) supply. The 3.3VDC regulated voltage pin is available externally for connection to Hall-effect sensors. The IC provides low power standby (less than 7mW) mode of operation that 3.3V power is cut off when VSP (Voltage Input) becomes less than 1.15V to provide further power efficient operation.

An integrated A/D Converter is used to acquire EFF load curve selection, temperature (internal temp sensing), and the VSP input that sets the voltage applied to the motor. An internal temperature sensor is interfaced to the ADC and resulting digital conversion data is

An internal temperature sensor is interfaced to the ADC and resulting digital conversion data i used to control the dynamic overcurrent setpoints as well as max overtemperature limit.

The protection functions include a supply under-voltage lockout (3.3V and 15VDC), over-speed protection, over-temperature limit and Over-current limitation protections. The reset circuitry includes a Power-On reset block and a reset input.

All devices do not require any programming. Default coefficients and system parameters are stored in internal ROM. The EFF input pin, used to adapt to specific motor and load to improve efficiency, can be used by means of two resistor pairs to choose one of 16 pre-stored load curves in ROM. DIR is a digital input pins which specify the motor direction command (CW or CCW).

All devices have an on-chip PLL to generate internal clocks. The PLL requires an external low frequency reference clock (32,768 Hz). The clock can be provided through an RC network connected to CLKIN and XTAL pins.

The IRDM983-025MB, IRDM983-035MB integrate high and low side gate drivers for applications up to 500V, it includes integrated Bootstrap FET that emulate bootstrap diode function and six power MOSFETs. The simplified block diagram is shown in Figure 1 in terms of hardware elements.

#### Simplified Block Diagram

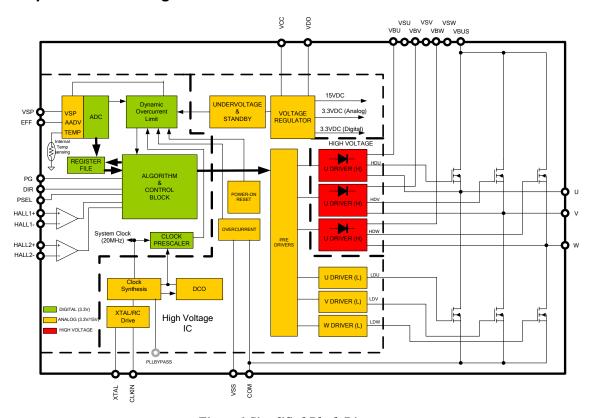


Figure 1 Simplified Block Diagram



## **Qualification Information**†

Qualifi	cation Level	Industrial <sup>††</sup> (per JEDEC JESD 47) Stress Test; Preconditioning, Temp Cycle, Autoclave, THB, HTSL, LTSL, IOL,			
Moisture Sensitivity Level PQFN		PQFN	MSL3 <sup>†††</sup> (per IPC/JEDEC J-STD-020) Floor Life Time; 168 hours Conditions; <30°C/60% RH Bake conditions; 125 +5/-0°C, 24 hours minimum		
FOD	Machine Model	Class B (per JEDEC Standard JESD22-A115) R1=0\Omega, C1=200pF+/-10\% Any part that passes after exposure to an ESD pulse of 100V, but fails after exposure to an ESD pulse of 150V.			
ESD	Human Body Model	Class 2 (per EIA/JEDEC standard EIA/JESD22-A114) R1=15000+/-1%, C1=100pF+/-10% Any part that passes after exposure to an ESD pulse of 1500V, but fails after exposure to an ESD pulse of 2000V.			
IC Latch-Up Test  Class I, Level A (per JESD78) Testing performed at room temp The failure criteria as defined in			n temperature ambient.		
RoHS	Compliant	Yes			

<sup>†</sup> Qualification standards can be found at International Rectifier's web site <a href="http://www.irf.com/">http://www.irf.com/</a>

Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information.

<sup>†††</sup> Higher MSL ratings may be available for the specific package types listed here. Please contact your International Rectifier sales representative for further information.

CLASS	TEST TYPE	TRICCER POLARITY	CONDITION OF UNITESTED INPUT PINS	TEST TEMPERATURE (±2°C)	V <sub>supply</sub> CONDITION	TRIGGER TEST CONDITIONS [6]	FAILURE CRITERIA						
	. Trest	POSITIVE see FIGURE	Max. Logic High [1] Min. Logic Low [1]			+(Inom+100 mA) or 1.5X Inom, whichever is greater [3]							
ı	I-TEST	NEGATIVE see FIGURE	Max. Logic High [1] Min. Logic Low [1]			Maximum operating voltage for each	-100 mA or5X Inom, whichever is greater in magnitude [4]						
	V <sub>supply</sub> OVER- VOLT-	see	Max. Logic High [1]			temperature	temperature	temperature	temperature	pin g	temperature	temperature	pin group per device specification
	AGE TEST	FIGURE	Min. Logic Low [1]			V <sub>supply</sub> [2]	1.4X Inom or Inom +10 mA						
	. —	POSITIVE see FIGURE	Max. Logic High [1] Min. Logic Low [1]			+(Inom+100 mA) or 1.5X Inom, whichever is greater [3]	whichever is greater [5]						
11	I-TEST	NEGATIVE see FIGURE	Max. Logic High [1] Min. Logic Low [1]	Maximum ambient	Maximum operating voltage for each	-100 mA or5X Inom, whichever is greater in magnitude [4]							
	V <sub>supply</sub> OVER - VOLT-	see	Max. Logic High [1]	operating temperature	V <sub>supply</sub> pin group per device specification	1.5 X max							
	AGE TEST	FIGURE Min. Logic Low[1]			V <sub>supply</sub> [2]								

Table 1.

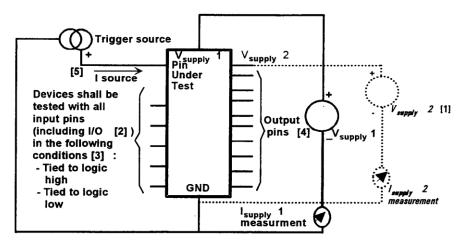


Figure 2.

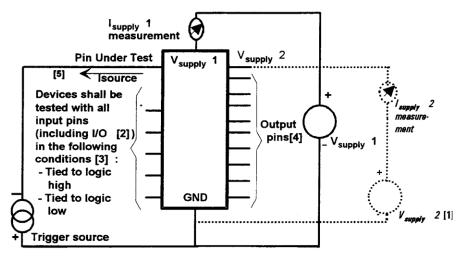
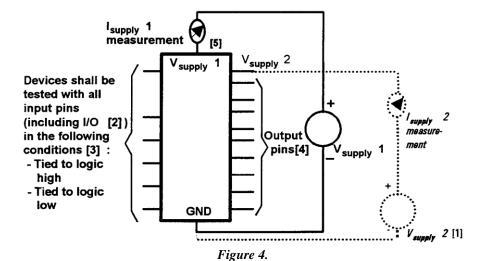


Figure 3.





#### IRDM983-025MB/-035MB Electrical Characteristics

#### Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to **VSS** unless otherwise stated in the table. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

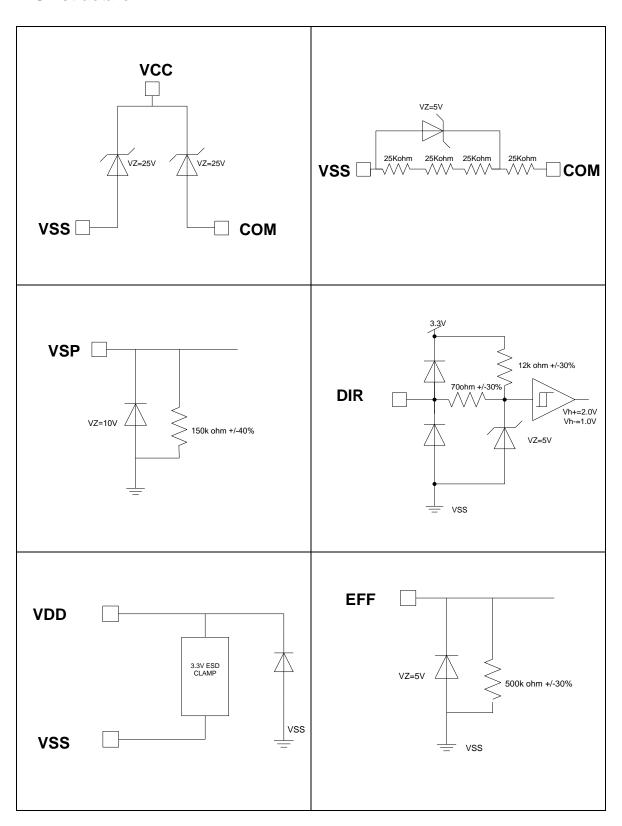
Ta=25C, unless otherwise stated.

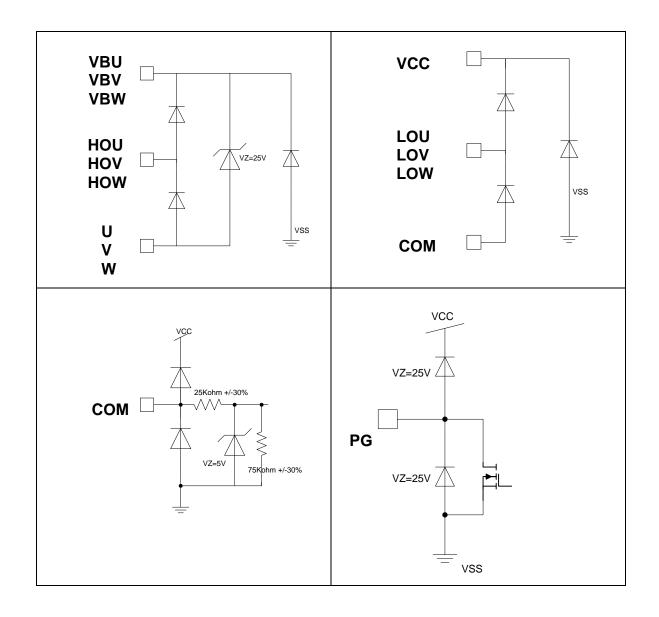
Symbol	Definition	Min.	Max.	Units	Condition
V <sub>ISO</sub>	Isolation voltage	1500	-	Vrms	AC 1 minute
VISO	Isolation voltage	1800	-	VIIIIS	AC 1 second
DCBUS	DC bus voltage	s voltage _ 500			IRDM983-025MB IRDM983-035MB
DCBUS <sub>STAT</sub>	DC bus voltage for PWM off - 600 V		IRDM983-025MB IRDM983-035MB VSP=0V, 1 minute, CO1=CO2 <sup>2)</sup>		
VBU, VBV, VBW	High-side floating absolute voltage	-0.3	525		
VSU, VSV, VSW	High-side floating supply offset voltage	VB - 25	VB + 0.3		
VCC	Low side power supply absolute voltage	-0.3	24		
	Drain current, IRDM983-035MB	-	3.9		Tc=25°C, Rth=2C/W
ID	Drain current, IRDM983-025MB	-	2.6	A	Tc=25°C, Rth=3C/W
I <sub>VDD</sub>	VDD current capability	-	2	^	TW=1ms
I <sub>VSP</sub>	VSP input current	-	5	mA	
COM	Power Ground	VCC - 24	VCC + 0.3		
$V_{HCOM}$	Hall Sensor input common mode voltage	-0.3	VDD		
$V_{PG}$	Open drain output motor evolution pulse	-0.3	VCC+0.3		
$V_{VSP}$	Analog input voltage VSP	-0.3	10.0	V	
$V_{DIR}$ $V_{EFF}$	Direction, Efficiency curve pins input voltage	-0.3	VDD+0.3		
VDD	3.3V voltage regulator output	-0.3	3.6		No short to ground
PD	Package power dissipation @ Tc ≤ +100 °C <sup>1)</sup>	-	5	W	
TJ	Junction temperature <sup>1)</sup>	-	150		
TS	Storage temperature <sup>1)</sup>	-55	150	°C	
TL	Lead temperature (soldering, 10 seconds) <sup>1)</sup>	-	260		

<sup>1)</sup> Guarantee by design, not tested at manufacturing

<sup>2)</sup> Output capacitance between VB-VS and VS-COM are same within +/-1%

#### ESD structure







#### **Recommended Operating Conditions**

For proper operation, the device should be used within the recommended conditions. All voltage parameters are absolute voltages referenced to **VSS** unless otherwise stated in the table.

The input/output logic timing diagram is shown in Fig. 1.

The VS and VSS offset rating are tested with all supplies biased at a 15 V (VCC) differential / 3.3V (VDD).

Power up and down sequences are not dependent on the order of VCC, DCBUS, and VSP for proper operation to start or

Symbol	Definition	Min.	Тур	Max.	Units	Condition
$V_U,V_V,V_W$	PWM output motor voltage <sup>1)</sup>	100	320	450	V	IRDM983-025MB IRDM983-035MB
$V_{PWMTR}$	Transient PWM output motor voltage †1)	-50	0	500		50ns transient period
		-	50	-		Fc=20kHz, DCBUS=300V, IO=140mArms, no heatsink, Ta=40C, IRDM983-025MB
Po	Output power <sup>1)</sup>	-	60	-	W	Fc=20kHz, DCBUS=300V, IO=200mArms, no heatsink, Ta=40C, IRDM983-035MB
VCC	Low side supply voltage	13.5 <sup>1)</sup>	15	16.5 <sup>1)</sup>		
V <sub>COM</sub>	COM-VSS voltage	-5	0	5		
V <sub>НСОМ</sub>	Hall sensor input voltage COMMON MODE	0.6	-	2.9		
$V_{\text{DIR}}, V_{\text{EFF}}$	Direction, Efficiency curve selection input pin voltage	0	-	VDD	V	
$V_{PG}$	Open drain output motor evolution pulse	0	-	VCC	v	
$V_{\text{VSP}}$	VSP input voltage	0	-	9.8		
VDD	3.3V voltage regulator output	3.0	-	3.6		Io=2mA
VDDstby	3.3V voltage regulator output when in stand by <sup>1)</sup>	0	-	0.8		VSP<1,15V for more than 5 s, Cout=20pF
$I_{VDD}$	VDD current capability	-	-	2	mA	TW=1ms
$C_{VDD}$	Capacitor at VDD	2.2	-	22	uF	
FCRmax	Carrier frequency	23.3k	23.9k	24.5k		$R_{CLKIN}$ =57.6 $K\Omega$ , $C_{CLKIN}$ =270 $pF$ $F_{CLKIN}$ =38.99 $kHz$
FCRtyp	Carrier frequency	18.1k	18.5k	18.9k	Hz	$R_{CLKIN}$ =75K $\Omega$ , $C_{CLKIN}$ =270pF $F_{CLKIN}$ =30.31kHz
FCRmin	Carrier frequency	14.5k	14.7k	15.0k		$R_{CLKIN}$ =95.3K $\Omega$ , $C_{CLKIN}$ =270pF $F_{CLKIN}$ =24.07kHz
R <sub>CLKIN</sub>	Resistor for RC oscillator <sup>2)</sup>	-	75K 39.2K	-	Ω	R=75kohm with C=270pF, C <sub>PCB</sub> =0pF Fc=18.83kHz R=75kohm with C=270pF, C <sub>PCB</sub> =5pF Fc=18.50kHz
C <sub>CLKIN</sub>	Capacitor for RC oscillator <sup>2)</sup>	-	270 470	-	pF	R=39.2kohm with C=470pF, C <sub>PCB</sub> =0pF Fc=20.75kHz R=39.2kohm with C=470pF, C <sub>PCB</sub> =5pF Fc=20.54kHz
TA	Ambient temperature <sup>1)</sup>	-40		125	°C	

<sup>†</sup>Operational for transient negative VS of - 50 V with a 50 ns pulse width is guaranteed by design. Refer to the Application Information section of this datasheet for more details.

C<sub>PCB</sub>: Board layout capacitance

<sup>1)</sup> Guarantee by design, not tested at manufacturing

<sup>2)</sup> Carrier Frequency is calculated by the following. FC=1/(((R+50) $\times$ (C+5 $\times$ 10<sup>-12</sup>+C<sub>PCB</sub>)+900 $\times$ 10<sup>-9</sup>) $\times$ 2.466)



#### Static Electrical Characteristics

 $(V_{CC}\text{-COM}) = (V_B\text{-}V_S) = 15 \text{ V}$ . TA = 25°C unless otherwise specified. The VSP and IIN parameters are referenced to  $V_{SS}$  and are applicable to all six channels. The VO and IO parameters are referenced to respective  $V_S$  and COM and are applicable to the respective output leads HO or LO. The  $V_{CCUV}$  parameters are referenced to  $V_{SS}$ . The  $V_{BSUV}$  parameters are referenced to  $V_S$ .

Symbol	Definition	Min	Тур	Max	Units	Test Conditions
IDSS	DC bus to COM leakage current, IRDM983-035MB	-	70	200	uA	DCBUS=500V, Tj=25C,per device
	DC bus to COM leakage current, IRDM983-025MB	-	50	100		
	MOSFET body diode voltage, IRDM983-025MB	-		1.0 <sup>2)</sup>		
VF	MOSFET body diode voltage, IRDM983-035MB	-		1.0 <sup>2)</sup>		IF=1A
VDD	VDD voltage	3.0	3.3	3.6		lo=2mA
VIH	Logic "1" input voltage	2.5	-	-		
VIL	Logic "0" input voltage	-	-	0.8		
VSPstbylow	Active to Standby mode VSP input negative going thresholds	1.05	1.15	1.25		
VSPstbyhigh	Standby to Active mode VSP input positive going thresholds	1.3	1.4	1.5	V	
VSPstbyhys	Standby mode VSP hysteresis	0.1	0.25	0.4		
VSPmin	VSP 0%duty	1.7	1.9	2.1		
VSPmax	VSP 100%duty	4.8	5.0	5.2		
VSP6step enter	VSP voltage that ensures enter in 6 step mode	8.0	8.8	9.68		500 ms continuously above threshold
VSP6step exit	VSP voltage that ensures exit from 6 step mode	8.0	8.8	9.68		200 ms continuously below threshold
$V_{HCOM}$	Hall sensor input voltage COMMON MODE	0.6	2	2.9		
$V_{HDIF}$	Hall sensor input voltage DIFFERENTIAL MODE	0.03	0.5	2.5		
$V_{NOG}$	Hall sensor input OP amp open loop gain <sup>1)</sup>	60	-	80	dB	Ta=-40 – 125C
$V_{HOO}$	Hall sensor input OP amp offset1)	-	1	-	mV	
$V_{IHSTH}$	Hall sensor input Schmitt Trigger input buffer hysteresis <sup>1)</sup>	=	1	-		
V <sub>HST+</sub>	Hall sensor input Digital Schmitt Trigger input buffer positive going voltage <sup>1)</sup>	-	2	-		
V <sub>HST-</sub>	Hall sensor input Digital Schmitt Trigger input buffer negative going voltage <sup>1)</sup>	-	1	-		
V <sub>CLKIN,TH+</sub>	CLKIN positive going threshold	2.5	-	-		
V <sub>CLKIN,TH</sub> -	CLKIN negative going threshold	-	-	0.8	V	
V <sub>CC,UVTH+</sub>	$V_{\text{CC}}$ supply undervoltage positive going Threshold	8	8.9	9.8		
V <sub>CC,UVTH-</sub>	$V_{\text{CC}}$ supply undervoltage negative going Threshold	7.4	8.2	9		
V <sub>CC,UVHYS</sub>	V <sub>CC</sub> supply undervoltage hysteresis	0.3	0.7	-		
V <sub>BS,UVTH+</sub>	V <sub>BS</sub> supply undervoltage positive going Threshold	8	8.9	9.8		
V <sub>BS, UVTH</sub> -	$V_{\text{BS}}$ supply undervoltage negative going Threshold	7.4	8.2	9	V	
$V_{BS,UVHYS}$	V <sub>BS</sub> supply undervoltage hysteresis	0.3	0.7	-		

## IRDM983-025MB, IRDM983-035MB

		ı	1	1		
$V_{ILIM1}$	Current Limit Input voltage 1 3)	450	520	590		Tc<92C (+/-12C)
V <sub>ILIM2</sub>	Current Limit Input voltage 2 3)	300	375	450	mV	Tc=92<96C (+/-12C)
V <sub>ILIM3</sub>	Current Limit Input voltage 3 3)	200	250	300		Tc=96<100C(+/-12C)
V <sub>ROCKILIM</sub>	Current Limit input voltage at Rotor Lock	200	250	300		
V <sub>ILIMHYS</sub>	Current Limit Input voltage hysteresis	-	60	-		
T <sub>OT+</sub>	Positive going over-temperature limit	88	100	112	°C	
T <sub>OT-</sub>	Negative going over-temperature limit	68	80	92		
TAC	Temp sensor absolute accuracy	0	-	12		
TES	Temp sensor resolution <sup>1)</sup>	0	-	3.25		
ICC	Vcc current	-	13	24	mA	
ICC <sub>STDBY</sub>	Vcc current at standby	-	0.10	0.20		
I <sub>VDD</sub>	3.3V output current	-	-	2		
$C_{VDD}$	External capacitor for VDD <sup>1)</sup>	2.2	-	22	uF	
PWM <sub>RES</sub>	PWM pulse width resolution	-	500	-	Counts	100ns resolution
MOD <sub>RESINT</sub>	Internal modulator amplitude resolution <sup>1)</sup>	-	1686	-		
Fc	PWM carrier frequency	19.6	20	20.4	kHz	CLKIN=32.768kHz
FXTAL	XTAL pin frequency <sup>1)</sup>	29.6	30.3	30.9		R=75kohm, C=270pF
		32.2	32.8	33.5		R=40.2kohm, C=470pF
RBS	Ron internal bootstrap diode	-	220	-	Ω	·
PD <sub>STBY</sub>	Standby power dissipation	=	1.5	3.0	mW	VSP<1.15V, DCBUS=0V
I <sub>DRV+</sub>	Internal driver gate drive sourcing current <sup>1)</sup>		6			V <sub>DRV</sub> =0 V,PW ≤10 μs
I <sub>DRV-</sub>	Internal driver gate drive sinking current <sup>1)</sup>	-	160	-	mA	V <sub>DRV</sub> =15 V, PW ≤10 µs
RON <sub>SPDFBK</sub>	Ron of SPDFBK pin	-	50	100	Ω	
		-	3	-		IRDM983-025MB
Rthj-c	Thermal resistance, junction to case <sup>1)</sup>	-	2	-	°C /W	IRDM983-035MB

<sup>1)</sup> Guaranteed by design, not tested at manufacturing

<sup>2)</sup> Tested at wafer probe

<sup>3)</sup> V<sub>ILIM1,2,3</sub> thresholds are tested at 25 degC. Temperature range is based on characterization only.



#### **Dynamic Electrical Characteristics**

 $V_{\text{CC}}$ =  $V_{\text{B}}$  = 15 V,  $V_{\text{S}}$  =  $V_{\text{SS}}$  = COM,  $T_{\text{A}}$  = 25°C, and  $C_{\text{L}}$  = 1000 pF unless otherwise specified.

Symbol	Definition	Min	Тур	Max	Units	Test Conditions
		-	3	-	Α	IRDM983-025MB, T <sub>J</sub> =25°C, $t_{SC}$ <20µs V <sup>+</sup> = 320V, V <sub>CC</sub> =15V
I <sub>csc</sub>	Short Circuit Drain Current <sup>1)</sup>	-	5	-		IRDM983-035MB, $T_J$ =25°C, $t_{SC}$ <20 $\mu$ s $V^+$ = 320V, $V_{CC}$ =15V
SCSOA	Short Circuit duration period <sup>1)</sup>	20000	-	-	ns	$V^{+}$ = 300V(IRDM983-025MB,- 35MB), $V_{CC}$ =+15V to 0V, line to line short
$t_RR$	Reverse recovery time 1)	-	80	-	ns	ID=1A, di/dt=100A/us
t <sub>ILIM</sub>	ILIM to PWM current limit propagation delay	-	3000	-	ns	$C_{LOAD} = 1nF, F_{CLKIN} = 32.768kHz$
		500	1000	1700		VILIM=2V, Ta=25C
t <sub>ILIMFIL</sub>	ILIM filter time <sup>1)</sup>	400	800	1400		VILIM=2V, Ta=125C
		600	1200	2000	ns	VILIM=2V, Ta=-40C
t <sub>HFILA</sub>	Hall differential input analog filter1)	-	1500	-		
t <sub>HFILD</sub>	Hall input digital filter delay <sup>1)</sup>	-	2500	-		F <sub>CLKIN</sub> =32.768kHz
t <sub>HALLSAT</sub>	HALL input response time from saturation <sup>1)</sup>	-	5000	-		
t <sub>HALLPG</sub>	HALL input to PG output propagation delay	-	5000	-		F <sub>CLKIN</sub> =32.768kHz
t <sub>vspact</sub>	VSP standby to PWM active time	14.0	17.5	22.0	ms	CVDD=2.2uF, VSP=0→5.4V, F <sub>CLKIN</sub> =32.768kHz
T <sub>VSPONDELAY</sub>	VSP active to PWM duty active	2.0	3.5	5.0	,	VSP from 1.8V to 2.6V, F <sub>CLKIN</sub> =32.768kHz
t <sub>VDDHOLD</sub>	VDD hold time at standby <sup>1)</sup>	4.9	5.0	5.1	S	CVDD=2.2uF, VSP=2→0V, F <sub>CLKIN</sub> =32.768kHz
t <sub>RLOCKDETECT</sub>	Rotor Lock detect time <sup>1)</sup>	4.9	5	5.1	3	VSP>2.1V,  Elec freq <3Hz, F <sub>CLKIN</sub> =32.768kHz
DT	Deadtime	-	1000	-		F <sub>CLKIN</sub> =32.768kHz
PW <sub>HIN</sub>	Internal high side minimum pulse width	-	400	-	ns	Not a final output of a part , F <sub>CLKIN</sub> =32.768kHz
$PW_{LIN}$	Internal low side minimum pulse width	-	100	-		Not a final output of a part , F <sub>CLKIN</sub> =32.768kHz
SPD <sub>OVER</sub>	Over speed <sup>1)</sup>	-	200	-		F <sub>CLKIN</sub> =32.768kHz
SPD <sub>PWMCHG</sub>	Block commutation to sine PWM change speed <sup>1)</sup>	-	3	-	Hz	1 consecutive electrical angle update period, F <sub>CLKIN</sub> =32.768kHz
SPD <sub>EFF1</sub>	EFF bending point 1 speed <sup>1)</sup>	-	33.33	_		F <sub>CLKIN</sub> =32.768kHz
SPD <sub>EFF2</sub>	EFF bending point 2 speed <sup>1)</sup>	-	83.33	-		F <sub>CLKIN</sub> =32.768kHz

<sup>1)</sup> Guaranteed by design, not tested at manufacturing

#### Figures of Input Circuit and Table

The following Figure shows the interconnect bonding among the HVIC and MOSFETs within a package.

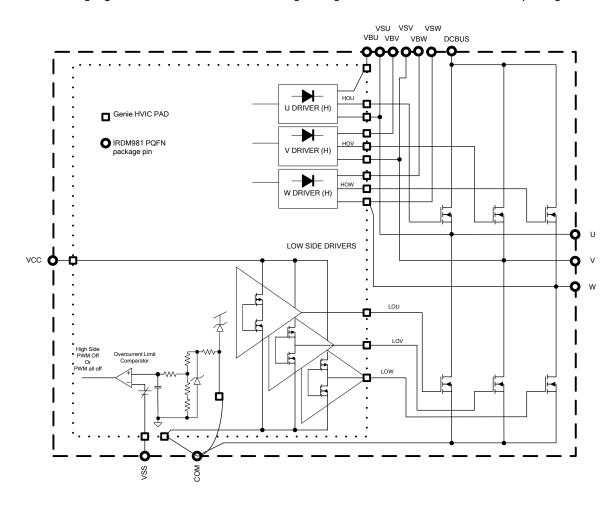


Figure 11 Connection diagram of VSS/COM and power pins/pads

The following Figures show the VSP input mapping, the Hall sensor input circuit, and the ISENSE pin input filter circuit.

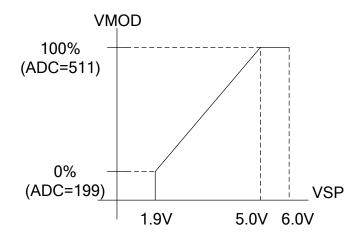


Figure 12 VSP Range and Thresholds

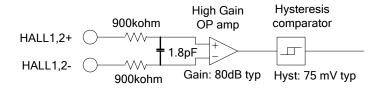


Figure 13 Hall sensor input circuit

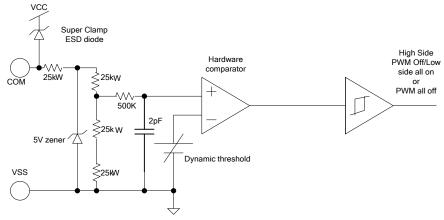


Figure 14 COM pin current limit comparator and analog filter

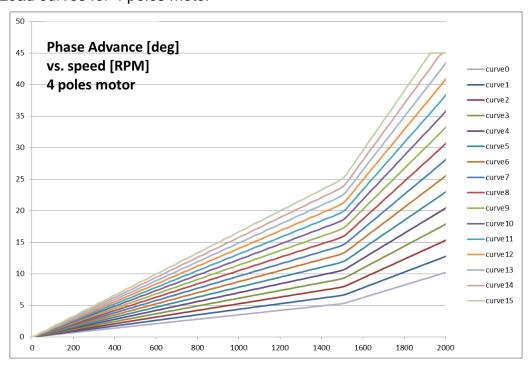
#### **Load Curves**

The following Table shows EFF pin mapping between input voltage and the advanced angle in degree per 50Hz of fundamental electrical frequency. Phase advance is by design clamped to be lower than 45 degrees at every frequency. At frequencies above 100 Hz the advancement is constant and it is kept to the same value at 100Hz.

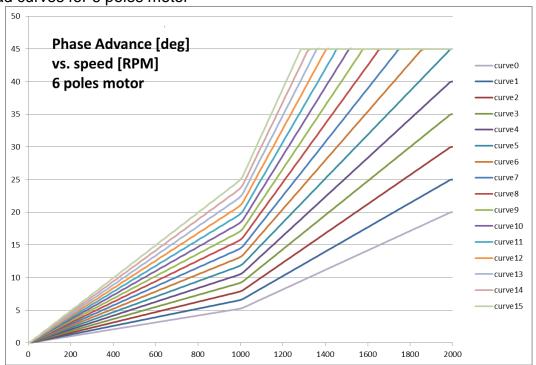
Select	Degree/50Hz	Frequency [Hz] @ advance=45deg	EFF input	EFF digital input
15	25.49	64.22	3.094V - 3.300V	152
14	24.15	65.75	2.888V - 3.087V	144
13	22.81	68.04	2.681V - 2.881V	136
12	21.47	70.34	2.475V - 2.675V	128
11	20.12	72.63	2.269V - 2.469V	120
10	18.78	75.69	2.063V - 2.262V	112
9	17.44	78.75	1.856V - 2.056V	104
8	16.10	81.80	1.650V - 1.850V	96
7	14.76	87.16	1.444V - 1.644V	88
6	13.42	92.51	1.238V - 1.437V	80
5	12.07	99.39	1.031V - 1.231V	72
4	10.73	Advance=40deg above 100Hz	0.825V – 1.025V	64
3	9.39	Advance=35deg above 100Hz	0.619V - 0.819V	56
2	8.05	Advance=30deg above 100Hz	0.413V - 0.612V	48
1	6.71	Advance=25deg above 100Hz	0.206V - 0.406V	40
Default = 0	5.37	Advance=20deg above 100Hz	0.000V - 0.200V	32

Table 2a EFF Parameters Selection

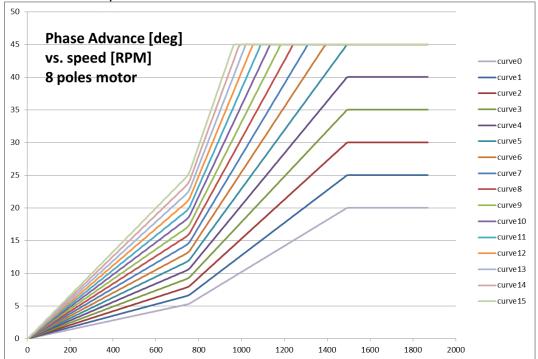
#### Load curves for 4 poles motor



Load curves for 6 poles motor



Load curves for 8 poles motor

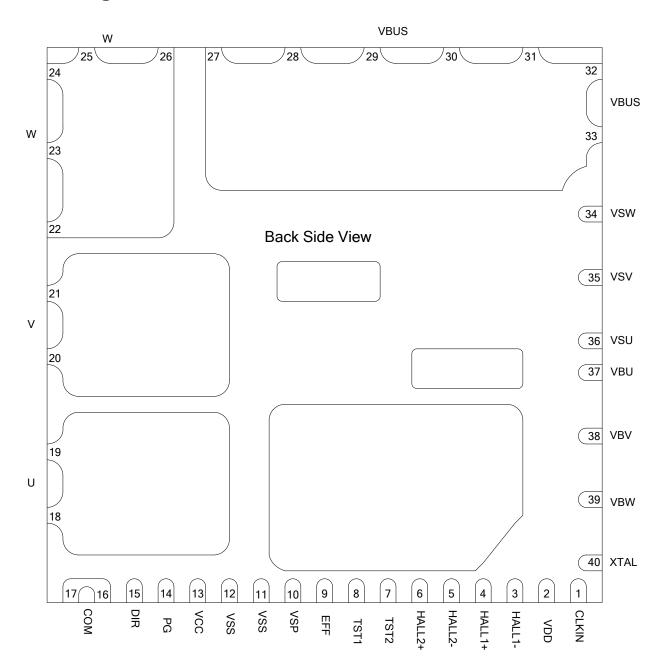




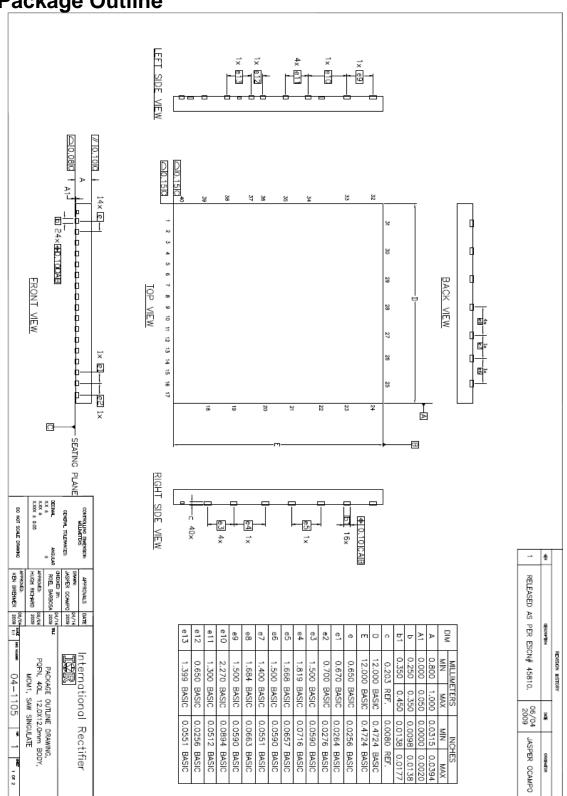
## **Lead Definitions**

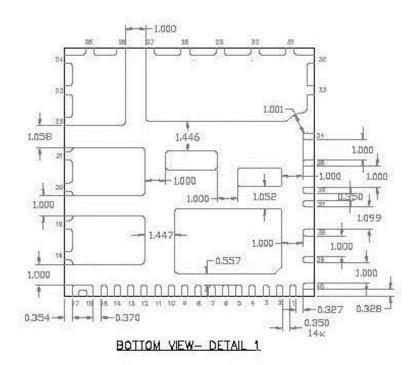
Symbol	Pin#	Description			
VSP	10	Voltage Set Point analog input. Provides the value of the PWM modulation index to the controller.			
PG	14	Provides speed feedback to through pulses per revolution. It is an open drain output 15V tolerant. Output is a square wave of a 3 pulses per electrical cycle of fundamental frequency			
DIR	15	Motor Direction Input (internally pulled up high = U→V→W)			
EFF	9	Load curve selection parameter Input for efficiency improvement			
XTAL	40	Clock buffer output			
CLKIN	1	Clock buffer input			
VSS	11	Logic ground			
COM	16,17	Analog input ITRIP and Power Ground and Low side MOSFET cource			
vcc	13	15V supply voltage			
HALL1+	4	Hall sensor 1 positive input			
HALL1-	3	Hall sensor 1 negative input			
HALL2+	6	Hall sensor 2 positive input			
HALL2-	5	Hall sensor 2 negative input			
TST1	8	Pin for factory testing – connect to VDD in normal application			
TST2	7	Pin for factory testing – connect to VSS in normal application			
VDD	2	3.3V output			
U	18,19	U phase output			
٧	20,21	V phase output			
w	22,23,24, 25,26	W phase output			
VBU	37	Phase U High side Bootstrap capacitor positive			
VBV	38	Phase V High side Bootstrap capacitor positive			
VBW	39	Phase W High side Bootstrap capacitor positive			
VSU	36	Phase U High side Bootstrap capacitor negative			
VSV	35	Phase V High side Bootstrap capacitor negative			
vsw	34	Phase W High side Bootstrap capacitor negative			
DCBUS	27,28,29, 30,31,32, 33	DC Bus voltage			

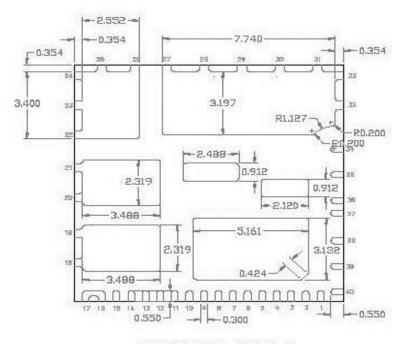
## **Lead Assignments**



**Package Outline** 



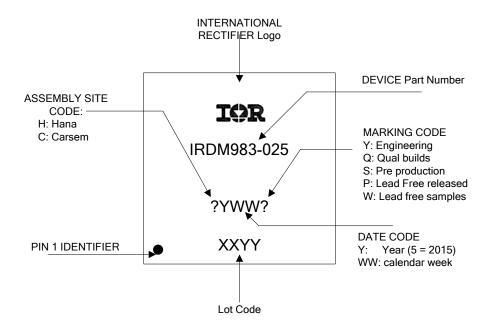




BOTTOM VIEW- DETAIL 2

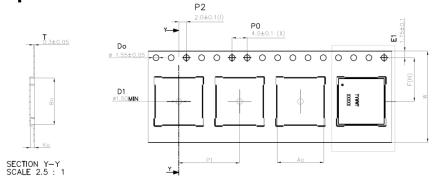
Dimension in mm<sup>2</sup>

## **Package Marking**



Part number	Internal MOSFET
IRDM983-025MB	500V 2A
IRDM983-035MB	500V 3A

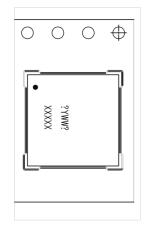
#### **Tape and Reel Details**

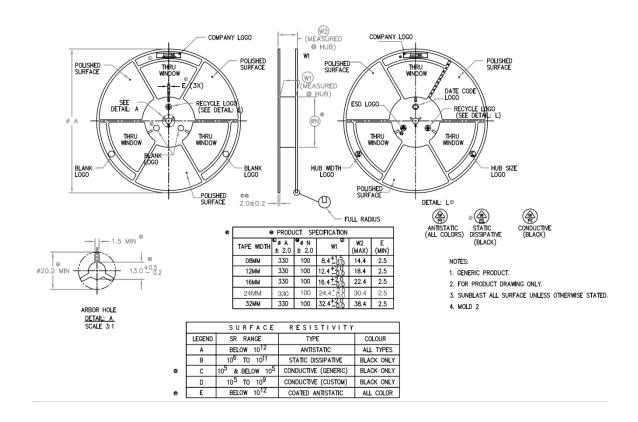


Ao	12.3	+/-	0.1
Во	12.3	+/-	0.1
Ko	1.10	+/-	0.1
F	11.50	+/-	0.1
P 1	16.00	+/-	0.1
W	24.00	+/-	0.3

- Measured from centerline of sprocket hole to centerline of pocket.
- (II) Cumulative tolerance of 10 sprocket holes is  $\pm$  0.20 .
- (III) Measured from centerline of sprocket hole to centerline of pocket.
- (IV) Other material available.

ALL DIMENSIONS IN MILLIMETERS UNLESS OTHERWISE STATED.





#### IRDM983-025MB, IRDM983-035MB

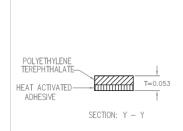
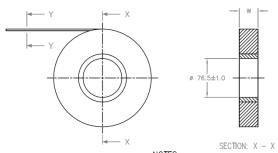


TABLE 2:

STANDARD COVER TAPE WIDTH (W ± 0.1)	CARRIER TAPE WIDTH
5.3, 5.4	8
9.2, 9.3	12
13.3	16
21.0, 21.3	24
25.5	32
37.5	44
49.5	56



NOTES:

- 1. THICKNESS: 0.048-0.058 mm.
- 2. STANDARD LENGTH: 300 m
- 3. TENSILE STRENGTH: 7.7 kg/mm sq.
- 4. ELONGATION: 120%
- 5. SURFACE RESISTIVITY: 10 ohms/SQ. MAX (STATIC DISSIPATIVE)
- 6. PEEL STRENGTH CONFORMS TO EIA SPEC. 55±25g
- 7. LUMINOUS TRANSMITTANCE: 91%
- 8. HAZE: 50%
- 9. OTHER COVER TAPE WIDTH REFER TO W14.08-04

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## Soldering temperature profile

The following soldering temperature profile is recommended. Any temperature which may exceed those indicated below is not recommended and may cause a permanent damage to the physical component such as deformation.

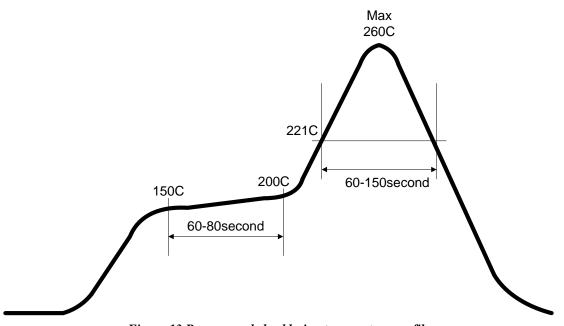


Figure 13 Recommended soldering temperature profile

Condition	Value	Remark
Temperature rise rate	3°C	
Temperature fall rate	6°C	
Number of reflow	2	
Manual soldering temperature	260°C	
Manual soldering time	10 second	

Table 3 Recommended soldering reflow condition

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